3. A Si sample is doped with 6×10<sup>16</sup> boron atoms/cm<sup>3</sup>. What is the resistivity of the sample at 300 K? Mobilities of electron and holes in Si are 1350 cm<sup>2</sup>/V-s and 480 cm<sup>2</sup>/V-s, respectively.

1.5 × 100 Toharge -19 Toharge

 $N_0 = 6110^6$   $M_0 = 6110^6$   $M_0 = 1350 m/v-s$   $M_0 = 480 cm^2/v-s$ 

 $\frac{1080 = ne^{2}}{90 = \frac{ne^{2}}{10}} = \frac{(2.5 \times 10^{10})^{2}}{(2.5 \times 10^{10})^{2}} = \frac{7.25 \times 10^{20}}{6 \times 10^{10}}$ 

 $\begin{array}{rcl}
& = 0.375 \times 10^{9} \\
& = 3750.
\end{array}$   $\begin{array}{rcl}
& = 3750.
\end{array}$ 

6 = g(304ln + gille)=  $1.6x10^{19}(2.5x10^{1350} + 1.5x10^{19480})$ 

= 4.392 x 10<sup>6</sup>

= 2 Pl - 1

A = 6

Resissairy = - - 41397 X/8 - 227686.7

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3+3